N-Channel Enhancement Mode Field Effect Transistor

Product Summary

ǒ V_{DS}	150V
ǒ I_D	90A
ǒ $R_{DS(ON)}$(at V_{GS}=10V)	11.8mq

ǒ 100% EAS Tested
ǒ 100% V_{DS} Tested

General Description

ǒ Split gate trench MOSFET technology
ǒ Excellent package for heat dissipation
ǒ High density cell design for low $R_{DS(ON)}$
ǒ Moisture Sensitivity Level 1
ǒ Epoxy Meets UL 94 V-0 Flammability Rating
ǒ Halogen Free

Applications

ǒ Power switching application
ǒ Uninterruptible

Typical Electrical and Thermal Characteristics Diagrams

Figure 1. Output Characteristics

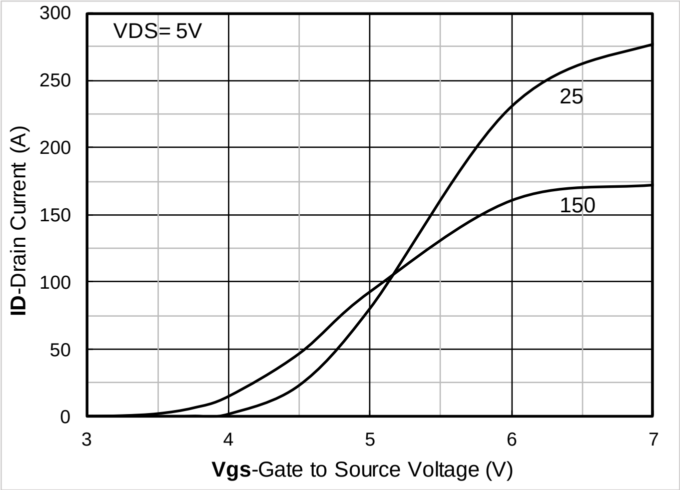


Figure 2. Transfer Characteristics

Figure 3. Capacitance Characteristics

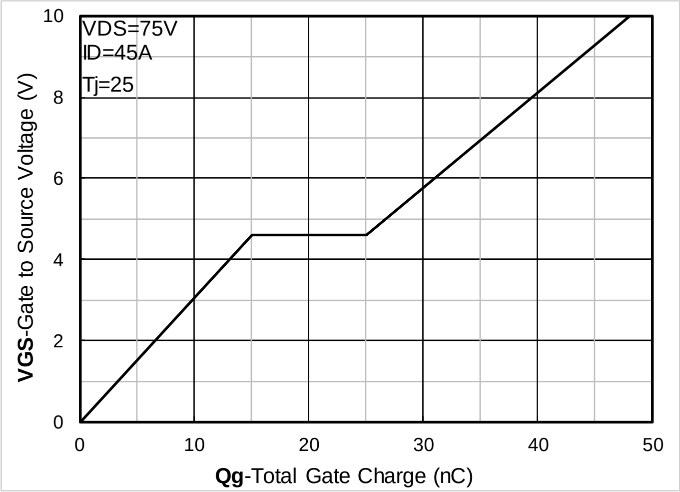


Figure 4. Gate Charge

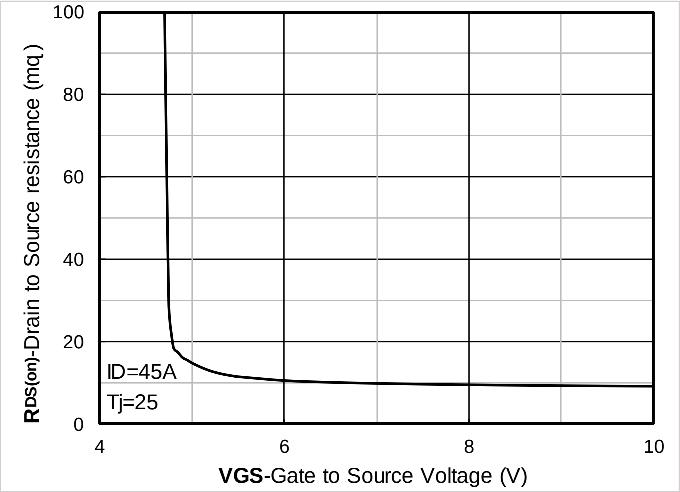


Figure 5. On-Resistance vs Gate to Source Voltage

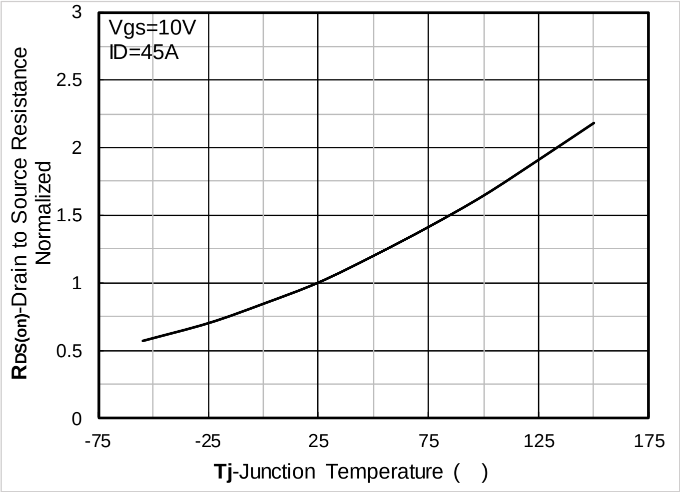


Figure 6. Normalized On-Resistance

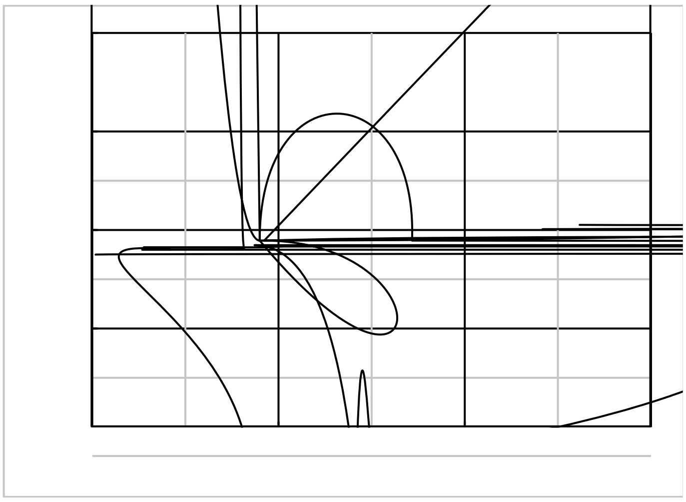


Figure 7. RDS(on) VS Drain Current

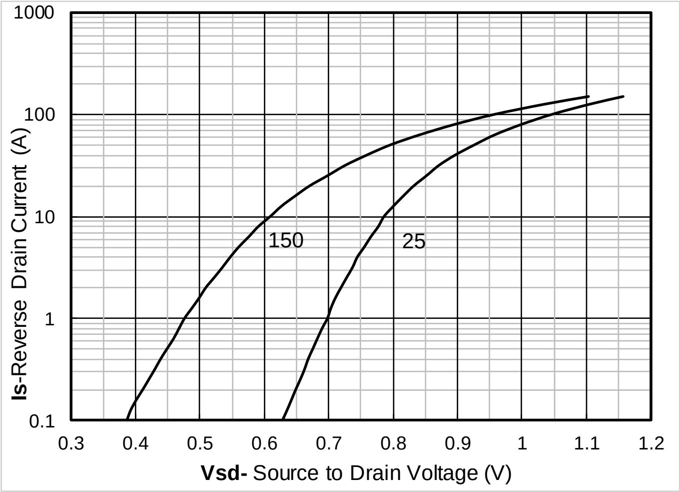


Figure 8. Forward characteristics of reverse diode

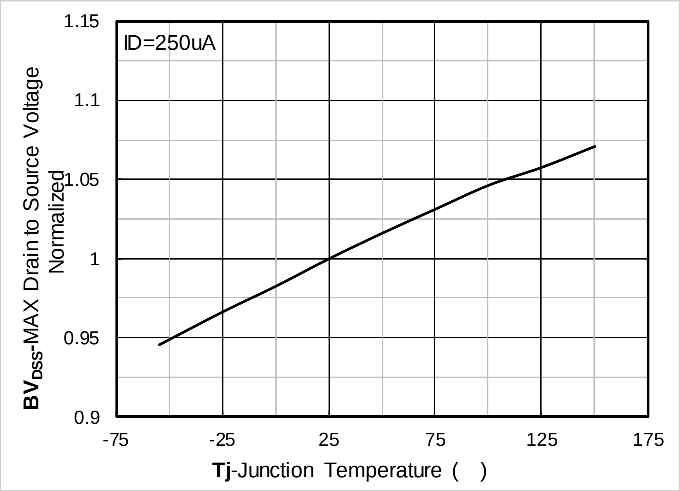


Figure 9. Normalized breakdown voltage

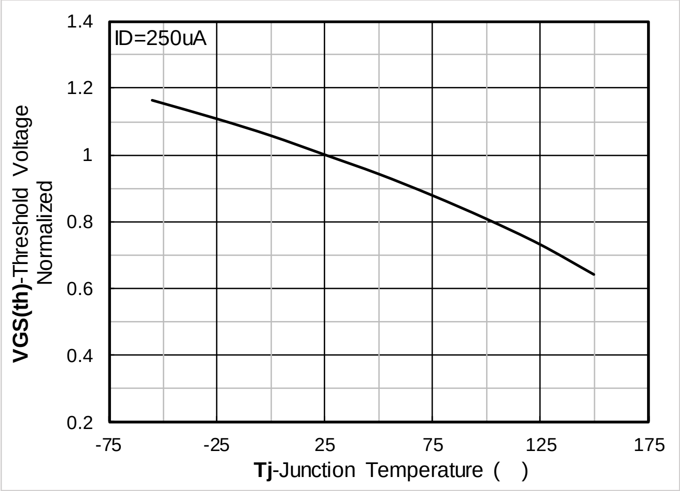
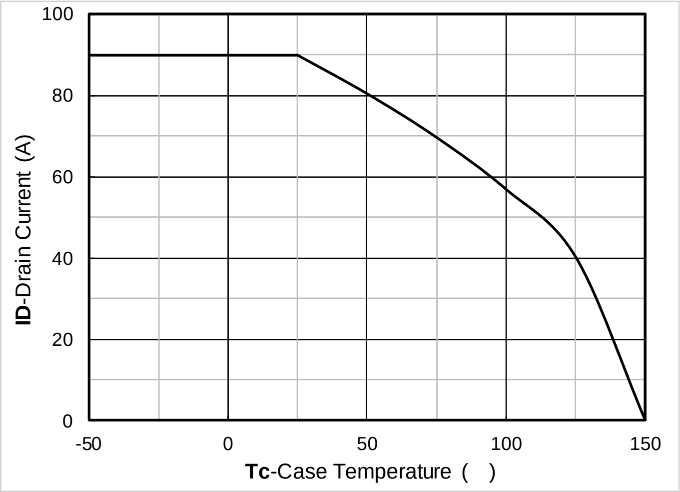


Figure 10. Normalized Threshold voltage



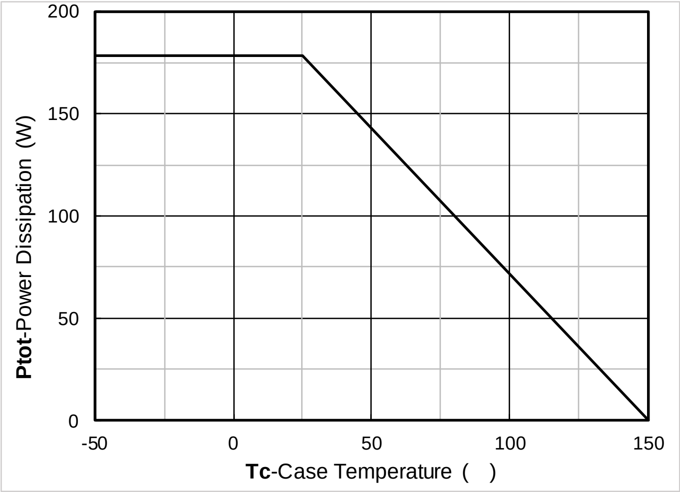


Figure 11. Current dissipation

Figure 12. Power dissipation

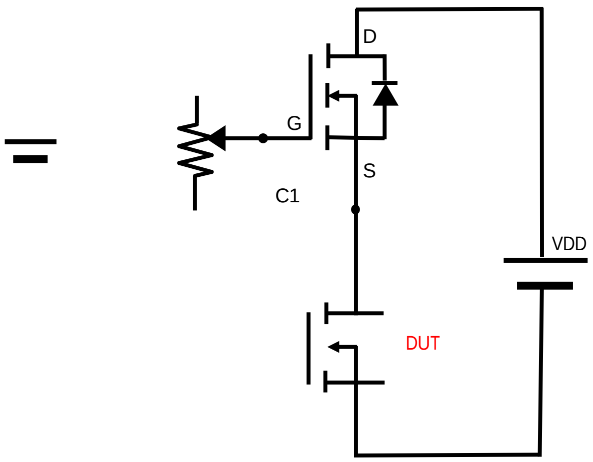


Figure B. Gate Charge Test Circuit & Waveform

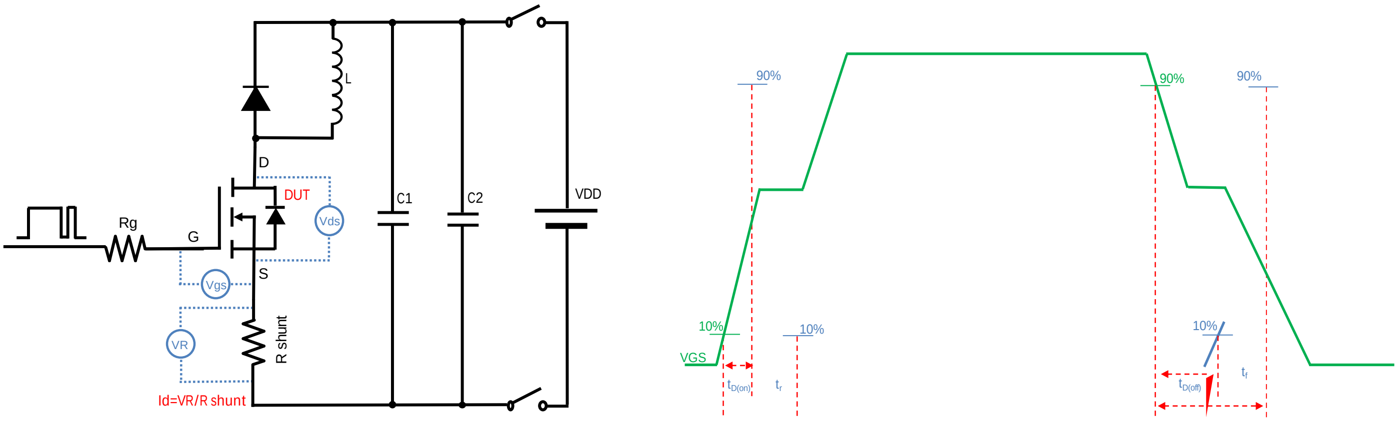


Figure C. Resistive Switching Test Circuit & Waveform

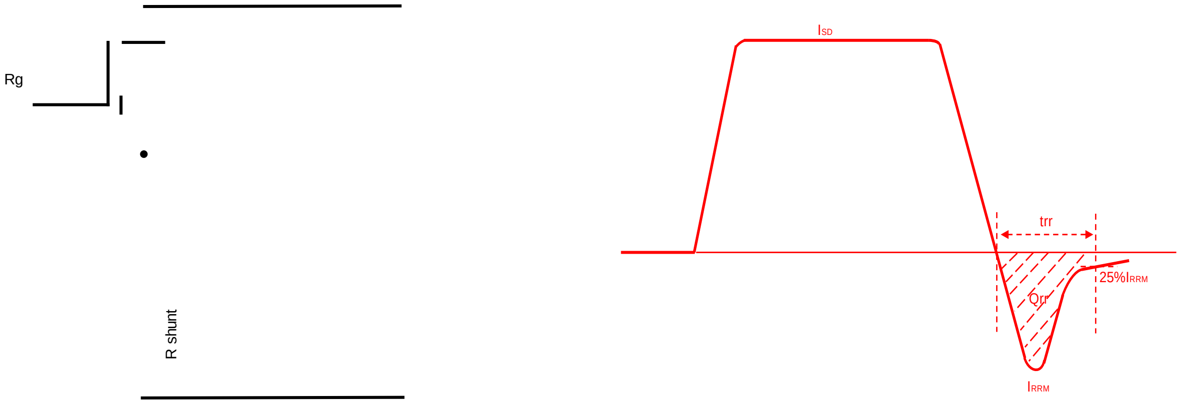


Figure D. Diode Recovery Test Circuit & Waveform